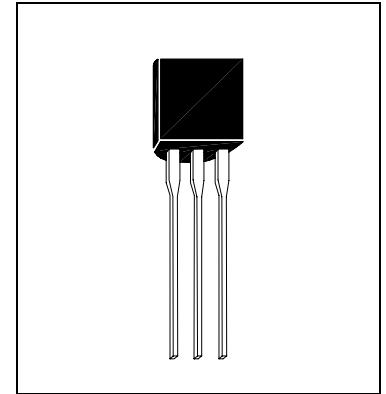




2N3906

PNP EPITAXIAL PLANAR TRANSISTOR



Description

The 2N3906 is designed for general purpose switching and amplifier applications.

Absolute Maximum Ratings

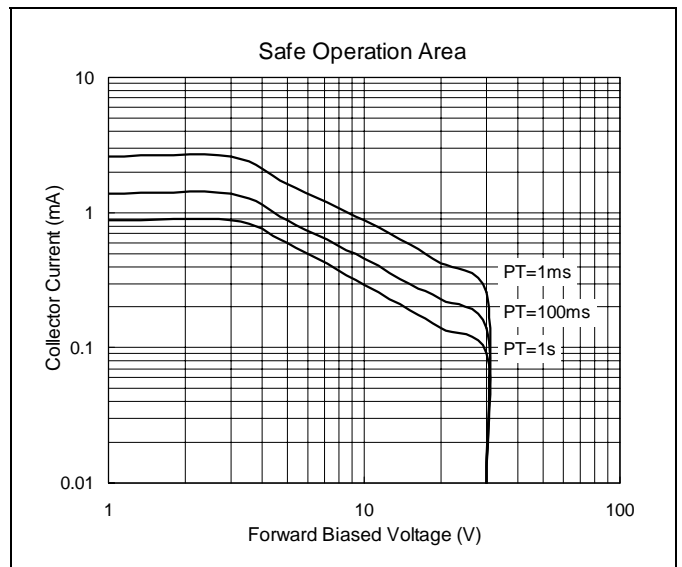
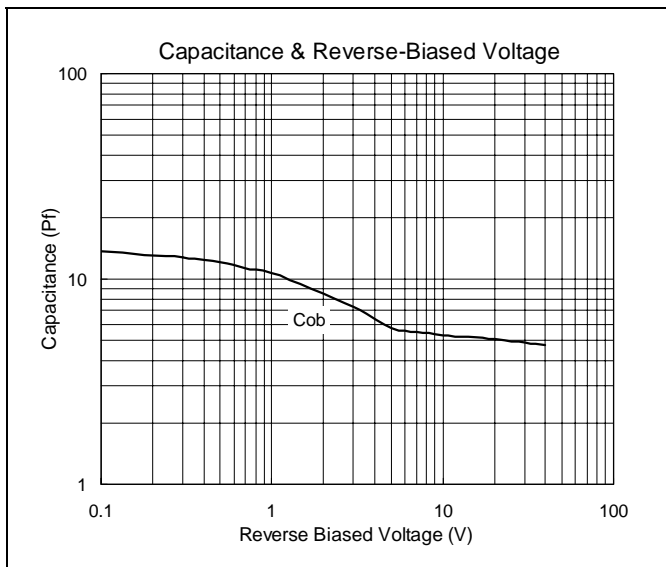
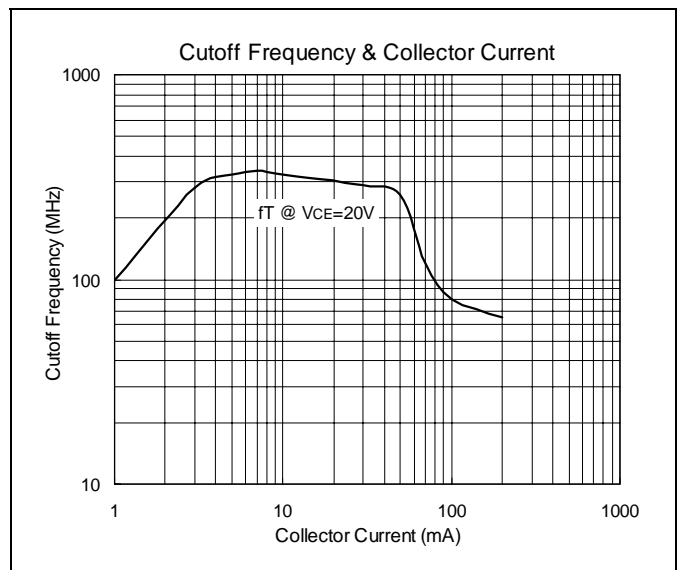
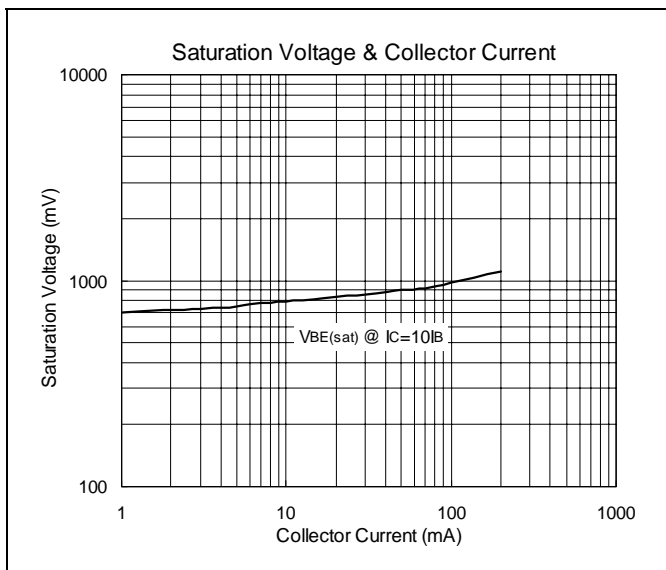
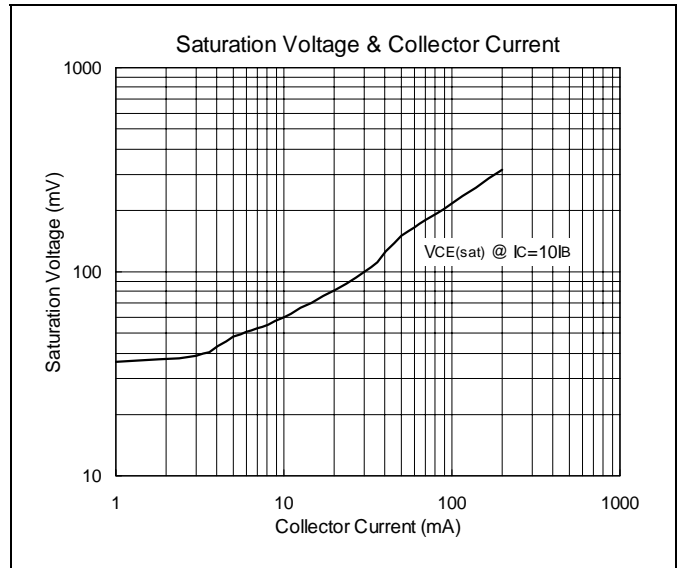
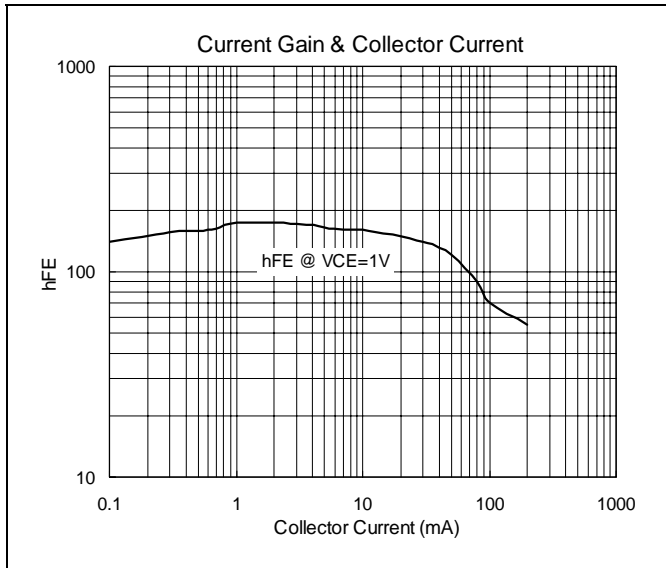
- Maximum Temperatures
Storage Temperature..... -55~+150°C
Junction Temperature..... +150°C Maximum
- Maximum Power Dissipation
Total Power Dissipation (Ta=25°C) 625 mW
- Maximum Voltages and Currents (Ta=25°C)
VCBO Collector to Base Voltage 40 V
VCEO Collector to Emitter Voltage 40 V
VEBO Emitter to Base Voltage 5.0 V
IC Collector Current 200 mA

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	40	-	-	V	IC=100uA, IE=0
BVCEO	40	-	-	V	IC=1mA, IB=0
BVEBO	5.0	-	-	V	IE=10uA, IC=0
ICEX	-	-	50	nA	VCE=30V, VBE=3V
VCE(sat)1	-	-	250	mV	IB=1mA, IC=10mA
VCE(sat)2	-	-	400	mV	IB=5mA, IC=50mA
VBE(sat)1	650	-	850	mV	IB=1mA, IC=10mA
VBE(sat)2	-	-	950	mV	IB=5mA, IC=50mA
hFE1	60	-	-		VCE=1V, IC=100uA
hFE2	80	-	-		VCE=1V, IC=1mA
hFE3	100	-	300		VCE=1V, IC=10mA
hFE4	60	-	-		VCE=1V, IC=50mA
hFE5	30	-	-		VCE=1V, IC=100mA
fT	250	-	-	MHz	VCE=20V, IC=10mA,, f=100MHz
Cob	-	-	4.0	pF	VCB=5V, IE=0, f=1MHz

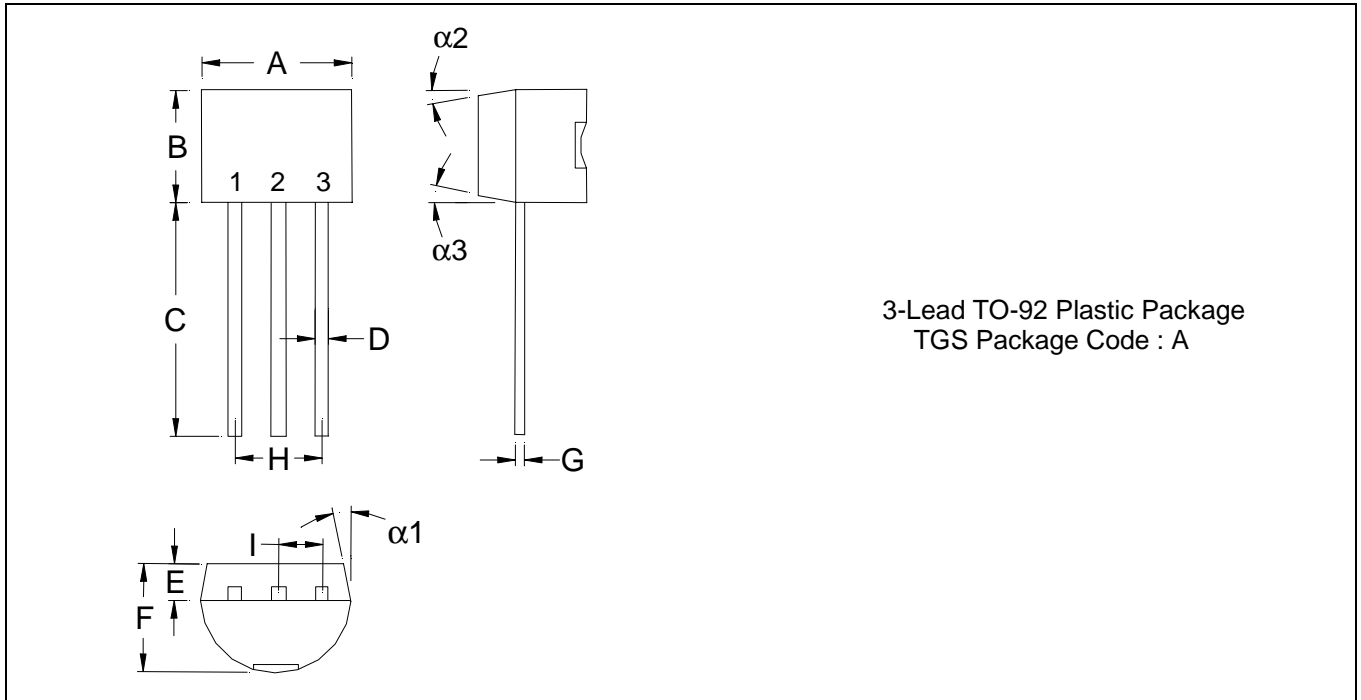


Characteristics Curve





TO-92 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1704	0.1902	4.33	4.83	G	0.0142	0.0220	0.36	0.56
B	0.1704	0.1902	4.33	4.83	H	-	*0.1000	-	*2.54
C	0.5000	-	12.70	-	I	-	*0.0500	-	*1.27
D	0.0142	0.0220	0.36	0.56	$\alpha 1$	-	*5°	-	*5°
E	-	*0.0500	-	*1.27	$\alpha 2$	-	*2°	-	*2°
F	0.1323	0.1480	3.36	3.76	$\alpha 3$	-	*2°	-	*2°